

REMARKS**I. Introduction**

In response to the pending Office Action, Applicants have amended claim 1 in order to further clarify the subject matter of the present invention and to overcome the § 112 rejections. The limitations of claim 4 have been incorporated into claim 1. Claims 4 and 6-39, and 50 have been cancelled, without prejudice. Claims 40-49 were previously cancelled. As such, the § 112 rejection of claims 6-50 is moot. No new matter has been added.

For the reasons set forth below, it is respectfully submitted that all pending claims are in condition for allowance.

II. The Rejection Of Claims 1-5 Under 35 U.S.C. § 112

Claims 1-5 were rejected under 35 U.S.C. § 112, first paragraph, because it is alleged that the specification does not provide enablement for any III-V Nitride semiconductor epitaxial form. Applicants respectfully traverse the rejections for at least the following reasons.

In the pending Office Action, the Examiner has alleged that the specification teaches, in a rather precise manner, specific growth conditions that would allow for an AlN layer having the crystal structure as recited to be formed on the silicon carbide substrate and that there is no teaching of how to form any other III-V Nitride semiconductor epitaxial film. As claim 1 has incorporated the limitations of claim 4 to recite that 4H-AlN is formed in contact with the substrate, Applicants assert that amended claim 1, and all pending dependent claims thereon are indeed supported in the specification.

Accordingly, as each of claims 1-3 and 5 are enabled by the specification, Applicants respectfully request that the § 112 rejections be withdrawn.

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III. Conclusion

Having fully responded to all matters raised in the Office Action, Applicants submit that all claims are in condition for allowance, an indication of which is respectfully solicited.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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